Gallardo-HernÃ¡ndez Salvador

List of Publications by Year
in descending order

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Version: 2024-02-01

55 papers	373 citations	933447 10 h-index	940533 16 g-index
55 all docs	55 docs citations	55 times ranked	471 citing authors

#	ARTICLE	IF	CITATIONS
1	Sol-gel synthesis of Ag-loaded TiO2-ZnO thin films with enhanced photocatalytic activity. Journal of Alloys and Compounds, 2019, 779, 908-917.	5.5	53
2	Study of the heavily p-type doping of cubic GaN with Mg. Scientific Reports, 2020, 10, 16858.	3.3	25
3	Effect of the immersion in CdCl2 and annealing on physical properties of CdS:F films grown by CBD. Journal of Physics and Chemistry of Solids, 2013, 74, 611-615.	4.0	24
4	As4 overpressure effects on the phase purity of cubic GaN layers grown on GaAs substrates by RF-MBE. Applied Surface Science, 2015, 353, 588-593.	6.1	15
5	CdS/CdTe Heterostructures for Applications in Ultra-Thin Solar Cells. Materials, 2018, 11, 1788.	2.9	15
6	Graded composition CdxZn1â^'xTe films grown by Isothermal Close Space Sublimation technique. Solar Energy Materials and Solar Cells, 2015, 138, 17-21.	6.2	14
7	Enhancement of CdS/CdTe solar cells by the interbuilding of a nanostructured Te-rich layer. Materials Research Express, 2017, 4, 086403.	1.6	14
8	Reconstruction of original indium distribution in InGaAs quantum wells from experimental SIMS depth profiles. Physica B: Condensed Matter, 2014, 453, 53-58.	2.7	12
9	Up and Down Conversion Photoluminescence from Er, Yb and Li Doped Y₂O₃Phosphors and Composites Films with PMMA. ECS Journal of Solid State Science and Technology, 2016, 5, R129-R135.	1.8	12
10	Study of structural properties of cubic InN films on GaAs(001) substrates by molecular beam epitaxy and migration enhanced epitaxy. Journal of Applied Physics, 2013, 113, 214308.	2.5	11
11	Study of Atomic Hydrogen Concentration in Grain Boundaries of Polycrystalline Diamond Thin Films. Applied Sciences (Switzerland), 2021, 11, 3990.	2.5	11
12	Voc enhancement of a solar cell with doped Li + -PbS as the active layer. Superlattices and Microstructures, 2018, 118, 137-144.	3.1	10
13	Characterization of n-GaN / p-GaAs NP heterojunctions. Superlattices and Microstructures, 2019, 136, 106298.	3.1	10
14	Cesium ion sputtering with oxygen flooding: Experimental SIMS study of work function change. Applied Surface Science, 2008, 254, 4961-4964.	6.1	9
15	SIMS characterization of segregation in InAs/GaAs heterostructures. Applied Surface Science, 2008, 255, 1341-1344.	6.1	9
16	Probability of ionization of sputtered particles as a function of their energy. Applied Surface Science, 2008, 254, 2059-2066.	6.1	8
17	Self-assembly of compositionally modulated Ga1â^'xMnxAs multilayers during molecular beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	8
18	Electrical, Optical and Structural Properties of SnO₂:Sb:F Thin Films Deposited from Sn(acac)₂by Spray Pyrolysis. ECS Journal of Solid State Science and Technology, 2016, 5, Q101-Q107.	1.8	8

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19	Ionization probability of sputtered particles as a function of their energy. Applied Surface Science, 2008, 254, 3801-3807.	6.1	7
20	Depth-profile analysis of nanostructures by SIMS: Depth resolution function. Bulletin of the Russian Academy of Sciences: Physics, 2008, 72, 895-898.	0.6	7
21	Structural and optical characterization of GaAs and InGaAs thin films deposited by RF magnetron sputtering. Optik, 2017, 145, 608-616.	2.9	7
22	Effects of heavy Si doping on the structural and optical properties of n-GaN/AlN/Si(111) heterostructures. Materials Research Express, 0, , .	1.6	7
23	SIMS depth profiling analysis of halogens in CdTe/CdS/TSO solar cells using Cs2M+ cluster ions. Applied Surface Science, 2008, 255, 1423-1426.	6.1	5
24	Characterization of Lanthanum-Aluminum Oxide Thin Films Deposited by Spray Pyrolysis. ECS Journal of Solid State Science and Technology, 2014, 3, N1-N6.	1.8	5
25	Formation of self-organized nano-surfaces on IIIâ€“V semiconductors by low energy oxygen ion bombardment. Materials Science in Semiconductor Processing, 2015, 37, 190-198.	4.0	5
26	Optical studies of nitrogen plasma for molecular beam epitaxy of InN. Journal of Applied Physics, 2020, 128, 215304.	2.5	5
27	Unveiling the influence of ZnTe and Te layers as part of the back-contact on CdTe solar cells performance. AIP Advances, 2021, 11, .	1.3	5
28	Electrical and optical properties of Si doped GaAs (631) layers studied as a function of the growth temperature. Journal of Crystal Growth, 2012, 347, 77-81.	1.5	4
29	Chemical analysis of obsidian by a SIMS/EDX combined system. Nuclear Instruments & Methods in Physics Research B, 2015, 343, 153-157.	1.4	4
30	Growth Mechanism and Properties of Self-Assembled InN Nanocolumns on Al Covered Si(111) Substrates by PA-MBE. Materials, 2019, 12, 3203.	2.9	4
31	Study of the surface chemistry, surface morphology, optical, and structural properties of InGaN thin films deposited by RF magnetron sputtering. Applied Surface Science, 2022, 586, 152795.	6.1	4
32	Cubic InxGa1â^'xN/GaN quantum wells grown by Migration Enhanced Epitaxy (MEE) and conventional Molecular Beam Epitaxy (MBE). Journal of Alloys and Compounds, 2022, 921, 165994.	5.5	4
33	Nitrogen Incorporation in Al₂O₃ Thin Films Prepared by Pulsed Ultrasonic Sprayed Pyrolysis. ECS Transactions, 2009, 25, 179-186.	0.5	3
34	Study of the oxygen incorporation in Al0.2Ga0.3In0.5P:Be layers grown by MBE employing a P-cracker cell. Journal of Crystal Growth, 2009, 311, 1650-1654.	1.5	3
35	SIMS depth profiling of semiconductor interfaces: Experimental study of depth resolution function. Surface and Interface Analysis, 2011, 43, 1277-1281.	1.8	3
36	High cubic phase purity and growth mechanism of cubic InN thin-films by Migration Enhanced Epitaxy. Thin Solid Films, 2018, 647, 64-69.	1.8	3

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37	Interference and electro-optical effects in cubic GaN/GaAs heterostructures prepared by molecular beam epitaxy. Journal of Applied Physics, 2020, 128, 125706.	2.5	3
38	Critical distance for secondary ion formation: Experimental SIMS measurements. Applied Surface Science, 2008, 255, 877-879.	6.1	2
39	Study of AlGaAs/GaAs quantum wells grown by molecular beam epitaxy on GaAs substrates subjected to different treatments. Journal of Crystal Growth, 2009, 311, 1666-1670.	1.5	2
40	Photoreflectance study of GaMnAs layers grown by MBE. Journal of Crystal Growth, 2011, 323, 344-347.	1.5	2
41	Study of interference effects on the photoluminescence of AlGaN/GaN quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 365-368.	0.8	2
42	SIMS depth profiling of â€˜frozenâ€™ samples: in search of ultimate depth resolution regime. Surface and Interface Analysis, 2017, 49, 145-148.	1.8	2
43	Optical characterization of InAs -layers grown by MBE at different substrate temperatures. Microelectronics Journal, 2008, 39, 1284-1285.	2.0	1
44	MBE growth and characterization of (100) and (631)-oriented modulation doped AlGaAs/GaAs heterostructures. Journal of Crystal Growth, 2013, 378, 88-91.	1.5	1
45	Two orders of magnitude reduction in the temperature dependent resistivity of Ga[sub 1â^'x]Mn[sub x]As grown on (6 3 1) GaAs insulating substrates. , 2013, , .		1
46	Optical and electrical study of cap layer effect in QHE devices with double-2DEG. Materials Research Society Symposia Proceedings, 2013, 1617, 31-36.	0.1	1
47	Magnetization in AIIIBV semiconductor heterostructures with the depletion layer of manganese. Low Temperature Physics, 2015, 41, 157-159.	0.6	1
48	Effects of growth temperature on the incorporation of nitrogen in GaNAs layers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	1
49	Structural and optical study of alternating layers of In and GaAs prepared by magnetron sputtering. Universitas Scientiarum, 2019, 24, 523-542.	0.4	1
50	SIMS Study of Modern Semiconductor Heterostructures.. , 2006, , .		0
51	Group III-nitrides nanostructures. , 2012, , .		0
52	On the gaps observed in high resolution x-ray diffraction scans and the wiggles in reciprocal space maps of high quality crystalline samples. , 2015, , .		0
53	In_xGa_{1-x}As obtained from independent target via co-sputtering deposition. Journal of Physics: Conference Series, 2017, 850, 012013.	0.4	0
54	Hyperbolic-tangent composition-graded InxGa1-xAs/GaAs (100) structures grown by molecular beam epitaxy. Materials Science in Semiconductor Processing, 2022, 142, 106486.	4.0	0

#	Article	IF	Citations
55	Indium incorporation at InxGa1-xN relaxed self-assembled nanostructures on Si substrates. Materials Science in Semiconductor Processing, 2022, 150, 106946.	4.0	0